Notification about the transfer of the semiconductor business

The semiconductor business of Panasonic Corporation was transferred on September 1, 2020 to Nuvoton Technology Corporation (hereinafter referred to as "Nuvoton"). Accordingly, Panasonic Semiconductor Solutions Co., Ltd. became under the umbrella of the Nuvoton Group, with the new name of Nuvoton Technology Corporation Japan (hereinafter referred to as "NTCJ").

In accordance with this transfer, semiconductor products will be handled as NTCJ-made products after September 1, 2020. However, such products will be continuously sold through Panasonic Corporation.

Publisher of this Document is NTCJ.

If you would find description "Panasonic" or "Panasonic semiconductor solutions", please replace it with NTCJ.

* Except below description page

"Request for your special attention and precautions in using the technical information and semiconductors described in this book"

Nuvoton Technology Corporation Japan



MOS FET FK6K02010L

FK6K02010L Silicon N-channel MOS FET

For switching

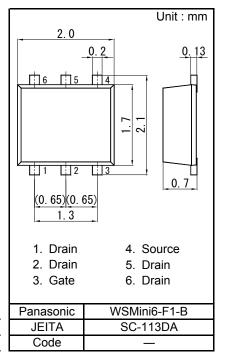
- Features
- Low drain-source On-state Resistance:RDS(on)typ. = $13 \text{ m}\Omega$ (VGS = 4.5 V) •
- Low drive voltage: 2.5 V drive
- Halogen-free / RoHS compliant ٠ (EU RoHS / UL-94 V-0 / MSL : Level 1 compliant)
- Marking Symbol : TA

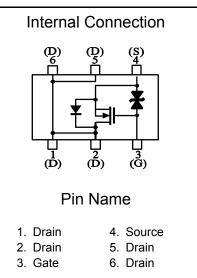
Packaging

Embossed type (Thermo-compression sealing): 3 000 pcs / reel (standard)

■ Absolute Maximum Ratings Ta = 25	Ъс		
Parameter	Symbol	Rating	Unit
Drain-source surrender voltage	VDSS	20	V
Gate-source surrender voltage	VGSS	±10	V
Drain current	ID	4.5	А
Peak drain current ^{*1}	IDp	18	А
Power dissipation *2	PD	700	mW
Channel temperature	Tch	150	°C
Operating ambient temperature	Topr	-40 to +85	°C
Storage temperature	Tstg	-55 to +150	°C
Note) *1 t = 10 μ s, Duty Cycle < 1%			

*2 Measuring on Glass epoxy board ($25.4 \times 25.4 \times t0.8$ mm) coated with copper foil, which has more than 300 mm² Absolute maximum rating without heat sink for PD is 150 mW.





Panasonic

MOS FET FK6K02010L

■ Electrical Characteristics Ta = 25 °C ± 3 °C

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Drain-source surrender voltage	VDSS	ID = 1 mA, VGS = 0	20			V
Drain-source cutoff current	IDSS	VDS = 20 V, VGS = 0			1.0	μA
Gate-source cutoff current	IGSS	VGS = ±8 V, VDS = 0			±10	μA
Gate threshold voltage	Vth	ID = 1.0 mA, VDS = 10.0 V	0.4	0.85	1.3	V
Drain-source ON resistance	RDS(ON)1	ID = 2.0 A, VGS = 4.5 V		13	17.5	mΩ
	RDS(ON)2	ID = 1.0 A, VGS = 2.5 V		16	28	
Forward transfer admittance	Yfs	ID = 1.0 A, VDS =10 V	3.0			S
Short-circuit input capacitance (Common source)	Ciss			1 730		pF
Short-circuit output capacitance (Common source)	Coss	VDS = 10 V, VGS = 0, f = 1 MHz		155		pF
Reverse transfer capacitance (Common source)	Crss			150		pF
Turn-on delay time *1	td(on)			19		ns
Rise time ^{*1}	tr	VDD = 10 V VGS = 0 to 4 V		30		ns
Turn-off delay time *1	td(off)	VGS = 0 to 4 V ID=1.0A		150		ns
Fall time ^{*1}	tf	10-1.0A		75		ns

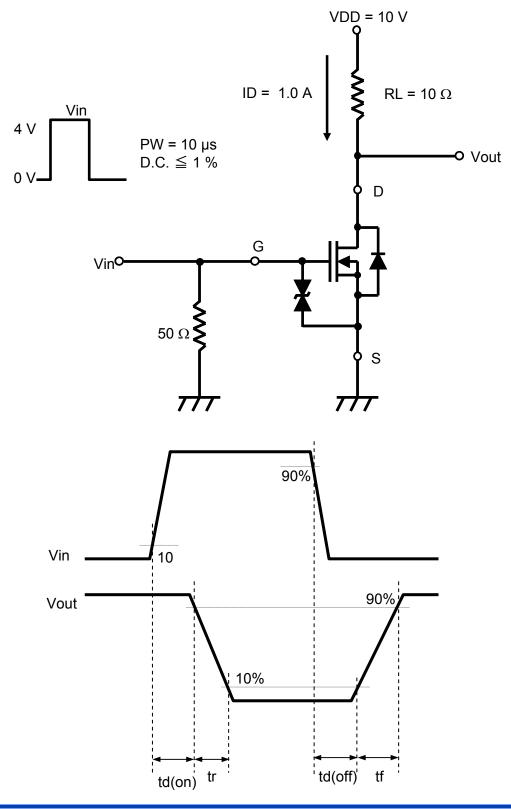
Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 Measuring methods for transistors.

2. *1 Measurement circuit for Turn-on Delay Time/Rise Time/Turn-off Delay Time/Fall Time

Doc No. TT4-EA-12566 Revision. 2

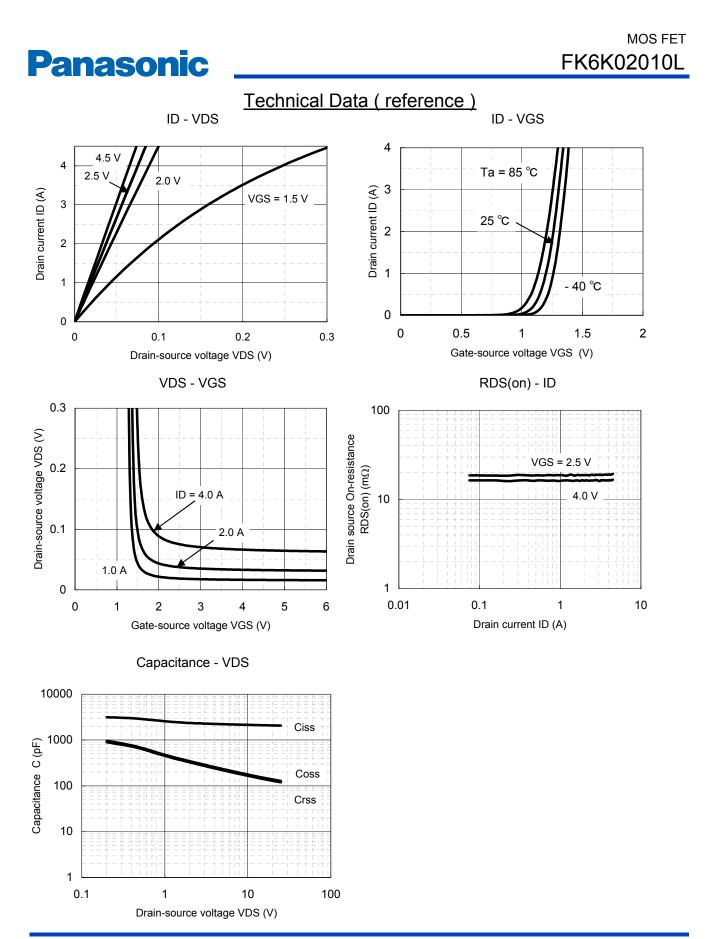


*1 Measurement circuit for Turn-on Delay Time/Rise Time/Turn-off Delay Time/Fall Time

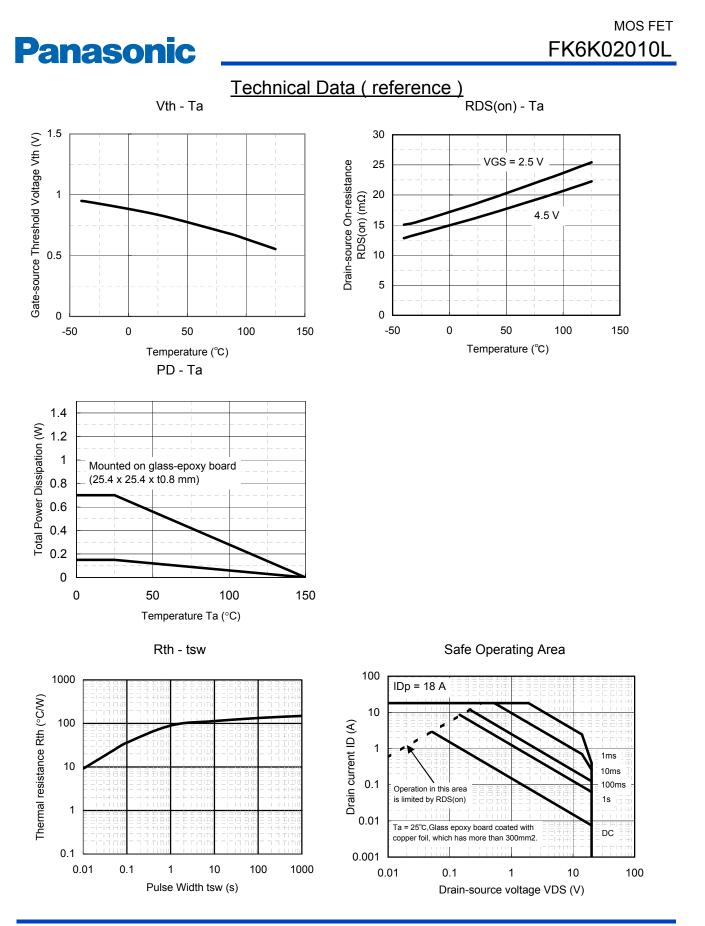


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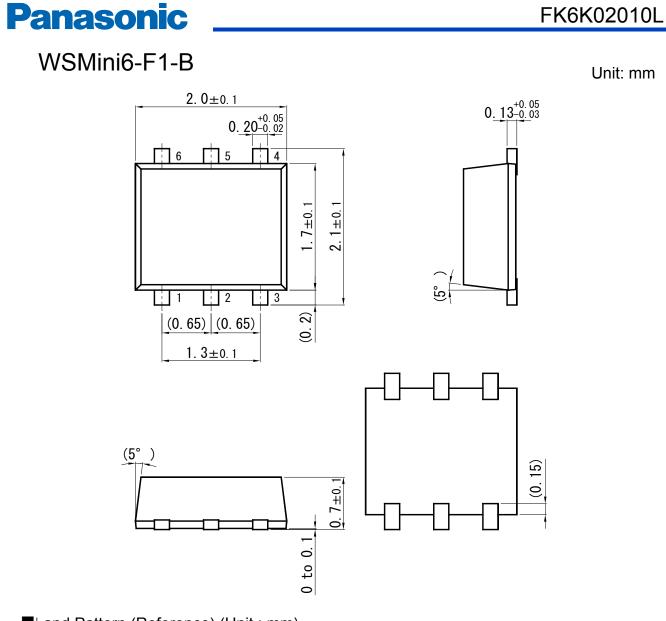
Established : 2010-06-07 Revised : 2013-07-01



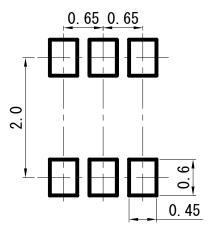




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Land Pattern (Reference) (Unit : mm)



MOS FET

Established : 2010-06-07 Revised : 2013-07-01

Request for your special attention and precautions in using the technical information and semiconductors described in this book

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- (2) The technical information described in this book is intended only to show the main characteristics and application circuit examples of the products. No license is granted in and to any intellectual property right or other right owned by Panasonic Corporation, Nuvoton Technology Corporation Japan or any other company. Therefore, no responsibility is assumed by our company as to the infringement upon any such right owned by any other company which may arise as a result of the use of technical information de-scribed in this book.
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